



**DMP2123L** 

#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

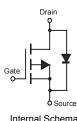
#### **Features**

- Low R<sub>DS(ON)</sub>
  - 72 mΩ @ $V_{GS}$  = -4.5V
  - 108 mΩ @V<sub>GS</sub> = -2.7V
  - 123 m $\Omega$  @V<sub>GS</sub> = -2.5V
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

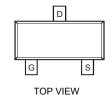
### **Mechanical Data**

- Case: SOT23
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (approximate)





SOT23



Internal Schematic

## Ordering Information (Note 4)

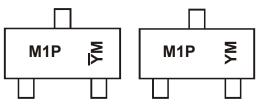
Part Number	Case	Packaging
DMP2123L-7	SOT-23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

## **Marking Information**

Chengdu A/T Site



Shanghai A/T Site

M1P = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or  $\overline{Y}$  = Year (ex: A = 2013)

M = Month (ex: 9 = September)

#### Date Code Key

Year	2007	2008	2009	2010	201	1 20	)12	2013	2014	2015	2016	2017
Code	U	V	W	X	Y		Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	2	1	5	6	7	Ω	0		N	D



# 

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	-20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 5) Continuous	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-3.0 -2.4	А
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-15	A
Body-Diode Continuous Current (Note 5)		I <sub>S</sub>	2.0	А

#### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$P_{D}$	1.4	W	
Thermal Resistance, Junction to Ambient (Note 5); Steady-State	$R_{ heta JA}$	90	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

Notes:

- 5. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t  $\leq$ 10s. 6. Repetitive Rating, pulse width limited by junction temperature.

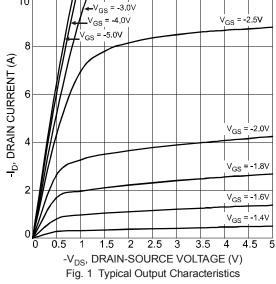
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

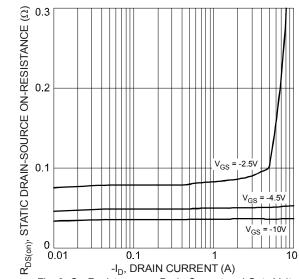
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC PARAMETERS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20		_	V	$I_D = -250 \mu A$ , $V_{GS} = 0 V$	
Zero Gate Voltage Drain Current $T_J = +25$ °C	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Body Leakage Current	I <sub>GSS</sub>	_	_	±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$	
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.6	_	-1.25	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
On State Drain Current (Note 7)	I <sub>D (ON)</sub>	-15		_	Α	$V_{GS} = -4.5V, V_{DS} = -5V$	
			51	72		$V_{GS} = -4.5V$ , $I_D = -3.5A$	
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(ON)</sub>	_	87	108	mΩ	$V_{GS} = -2.7V, I_D = -3.0A$	
			99	123		$V_{GS} = -2.5V$ , $I_D = -2.6A$	
Forward Transconductance (Note 7)		_	7.3	_	S	$V_{DS} = -10V$ , $I_D = -3.0A$	
Diode Forward Voltage (Note 5)	$V_{SD}$	_	0.79	-1.26	V	I <sub>S</sub> = -1.7A, V <sub>GS</sub> = 0V	
Maximum Body-Diode Continuous Current (Note 5)	Is	_	_	1.7	Α	_	
DYNAMIC PARAMETERS (Note 8)	DYNAMIC PARAMETERS (Note 8)						
Total Gate Charge	$Q_g$	_	7.3	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = -3.0A$	
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = -3.0A$	
Gate-Drain Charge	$Q_{gd}$	_	1.9	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = -3.0A$	
Turn-On Delay Time		_	12	_	ns		
Turn-On Rise Time Turn-Off Delay Time		_	20	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$	
		_	38	_	ns	$R_L = 10\Omega$ , $R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	41		ns	]	
Input Capacitance		_	443	_	pF	101111	
Output Capacitance	Coss	_	128	_	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	101		pF	1.50012	

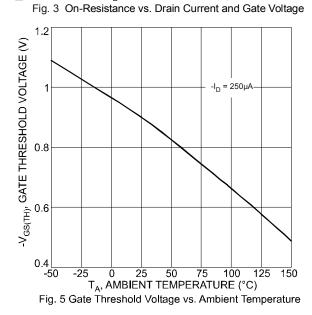
Notes: 7. Test pulse width  $t = 300 \mu s$ .

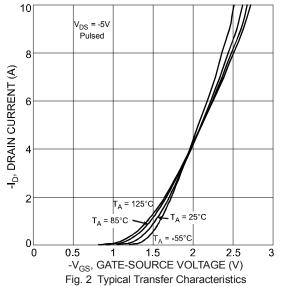
8. Guaranteed by design. Not subject to production testing.

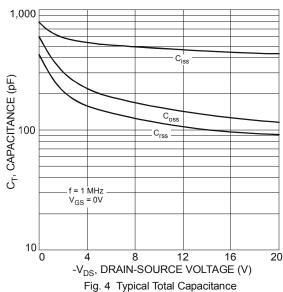












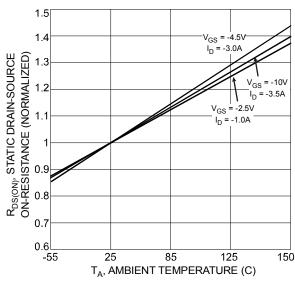


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



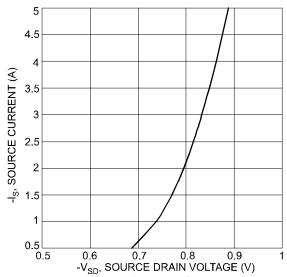
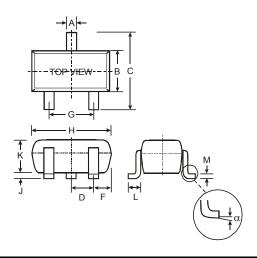


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

## **Package Outline Dimensions**

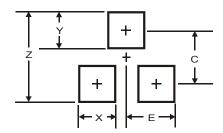
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23						
Dim	Min	Max				
Α	0.37	0.51				
В	1.20	1.40				
С	2.30	2.50				
D	0.89	1.03				
F	0.45	0.60				
G	1.78	2.05				
Н	2.80	3.00				
J	0.013	0.10				
K	0.903	1.10				
L	0.45	0.61				
M	0.085	0.180				
α	0°	8°				
All Dir	All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35



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